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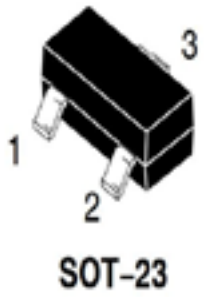
FDV301N
Digital FET , N-Channel

General Description

This N-Channel logic level enhancement mode field effect transistor is produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance. This device has been designed especially for low voltage applications as a replacement for digital transistors. Since bias resistors are not required, this one N-channel FET can replace several different digital transistors, with different bias resistor values.

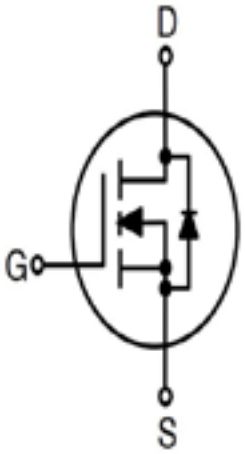
Features

- 25 V, 0.22 A continuous, 0.5 A Peak.
  $R_{DS(ON)}$ = 5 Ω @ V_{GS}= 2.7 V
  $R_{DS(ON)}$ = 4 Ω @ V_{GS}= 4.5 V.
- Very low level gate drive requirements allowing direct operation in 3V circuits. $V_{GS(th)}$ < 1.06V.
- Gate-Source Zener for ESD ruggedness. >6kV Human Body Model
- Replace multiple NPN digital transistors with one DMOS FET.



SOT-23

1 – Gate
2 – Source
3 – Drain



Absolute Maximum Ratings T_A = 25°C unless other wise noted

Symbol	Parameter	FDV301N	Units
V_{DSS}, V_{CC}	Drain-Source Voltage, Power Supply Voltage	25	V
V_{GSS}, V_I	Gate-Source Voltage, V_{IN}	8	V
I_D, I_O	Drain/Output Current - Continuous	0.22	A
		0.5	
P_D	Maximum Power Dissipation	0.35	W
T_J,T_{STG}	Operating and Storage Temperature Range	-55 to 150	°C
ESD	Electrostatic Discharge Rating MIL-STD-883D Human Body Model (100pf / 1500 Ohm)	6.0	kV
THERMAL CHARACTERISTICS			
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	357	°C/W

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Inverter Electrical Characteristics (T_A = 25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
$I_{O(off)}$	Zero Input Voltage Output Current	V_{CC} = 20 V, V_I = 0 V			1	μA
$V_{I(off)}$	Input Voltage	V_{CC} = 5 V, I_O = 10 μA			0.5	V
$V_{I(on)}$		V_O = 0.3 V, I_O = 0.005 A	1			V
$R_{O(on)}$	Output to Ground Resistance	V_I = 2.7 V, I_O = 0.2 A		4	5	Ω

Electrical Characteristics (T_A = 25 °C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA	25			V
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	I_D = 250 μA, Referenced to 25 °C		25		mV / °C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 20 V, V_{GS} = 0 V			1	μA
		T_J = 55°C			10	μA
I_{GSS}	Gate - Body Leakage Current	V_{GS} = 8 V, V_{DS} = 0 V			100	nA
ON CHARACTERISTICS (Note)						
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Temp. Coefficient	I_D = 250 μA, Referenced to 25 °C		-2.1		mV / °C
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 μA	0.70	0.85	1.06	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS} = 2.7 V, I_D = 0.2 A		3.8	5	Ω
		T_J =125°C		6.3	9	
		V_{GS} = 4.5 V, I_D = 0.4 A		3.1	4	
$I_{D(ON)}$	On-State Drain Current	V_{GS} = 2.7 V, V_{DS} = 5 V	0.2			A
g_{FS}	Forward Transconductance	V_{DS} = 5 V, I_D = 0.4 A		0.2		S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{DS} = 10 V, V_{GS} = 0 V, f = 1.0 MHz		9.5		pF
C_{oss}	Output Capacitance			6		pF
C_{rss}	Reverse Transfer Capacitance			1.3		pF
SWITCHING CHARACTERISTICS (Note)						
$t_{D(on)}$	Turn - On Delay Time	V_{DD} = 6 V, I_D = 0.5 A, V_{GS} = 4.5 V, R_{GEN} = 50 Ω		3.2	8	ns
t_r	Turn - On Rise Time			6	15	ns
$t_{D(off)}$	Turn - Off Delay Time			3.5	8	ns
t_f	Turn - Off Fall Time			3.5	8	ns
Q_g	Total Gate Charge	V_{DS} = 5 V, I_D = 0.2 A, V_{GS} = 4.5 V		0.49	0.7	nC
Q_{gs}	Gate-Source Charge			0.22		nC
Q_{gd}	Gate-Drain Charge			0.07		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
I_S	Maximum Continuous Drain-Source Diode Forward Current				0.29	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 0.29 A (Note)		0.8	1.2	V

Note:
Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2.0%.

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Typical Electrical Characteristics

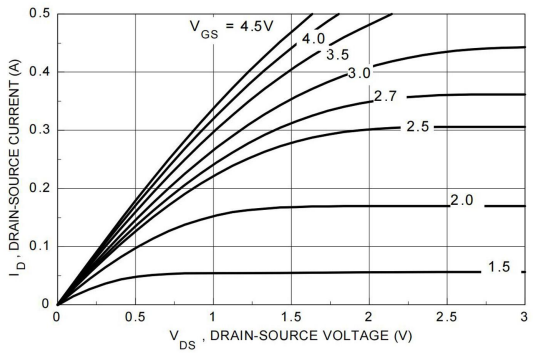


Figure 1. On-Region Characteristics.

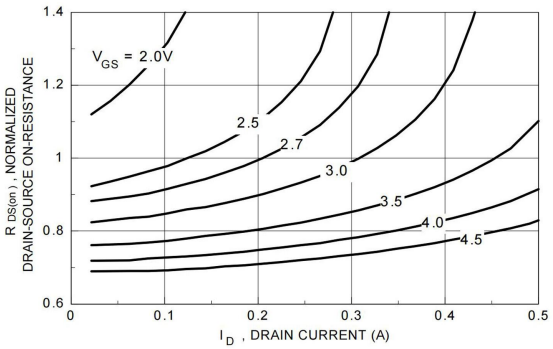


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

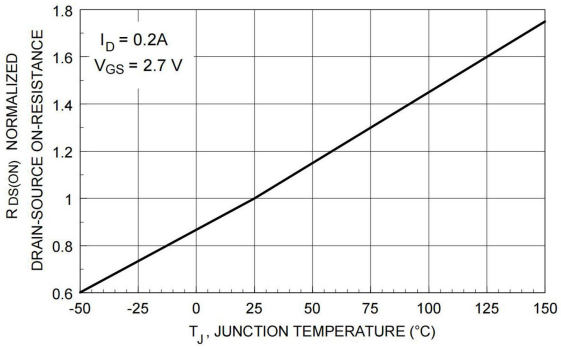


Figure 3. On-Resistance Variation with Temperature.

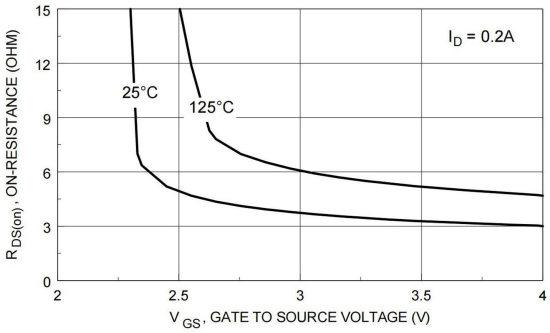


Figure 4. On Resistance Variation with Gate-To-Source Voltage.

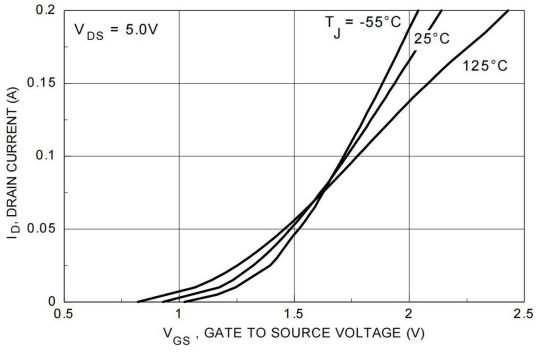


Figure 5. Transfer Characteristics.

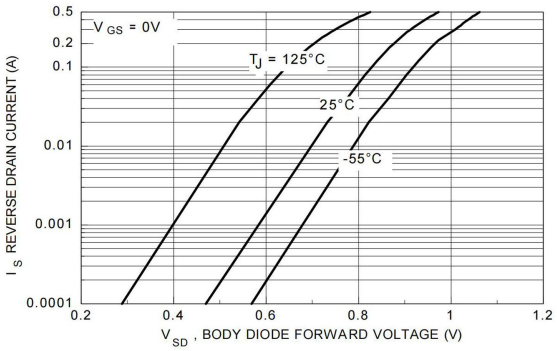


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

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Typical Electrical And Thermal Characteristics

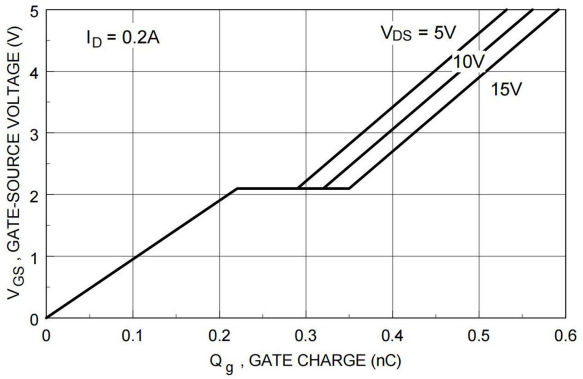


Figure 7. Gate Charge Characteristics.

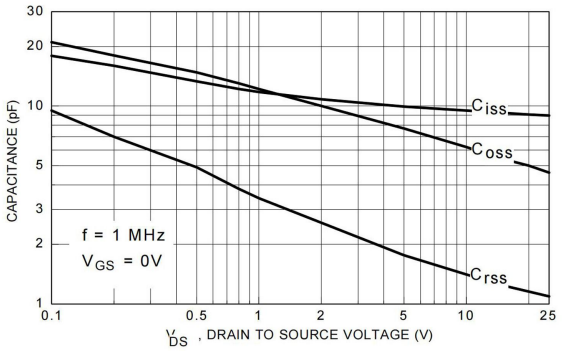


Figure 8. Capacitance Characteristics.

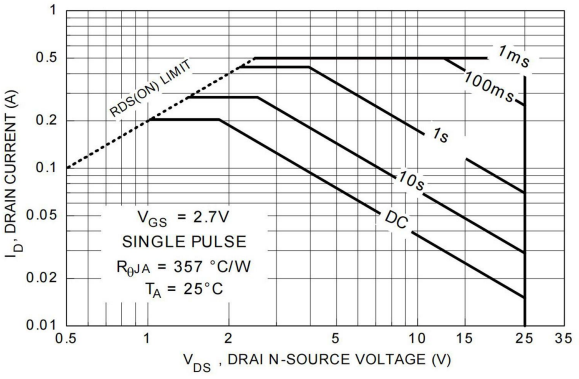


Figure 9. Maximum Safe Operating Area.

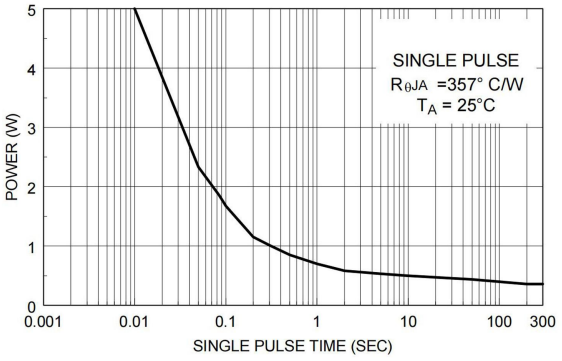


Figure 10. Single Pulse Maximum Power Dissipation.

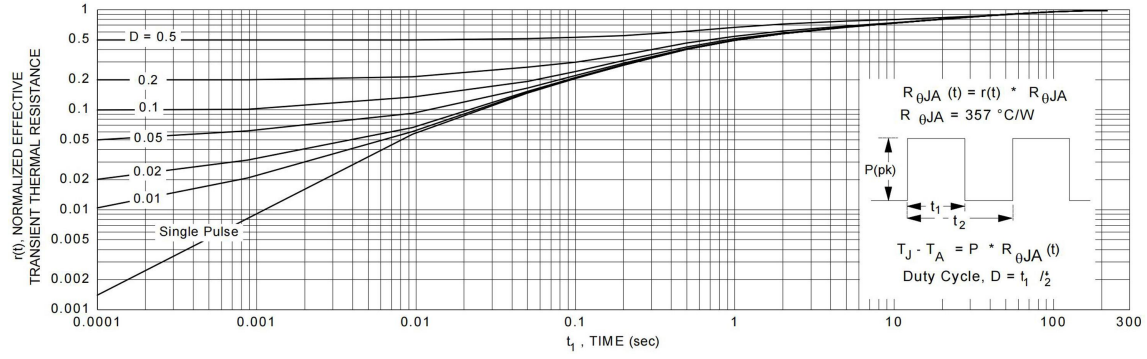


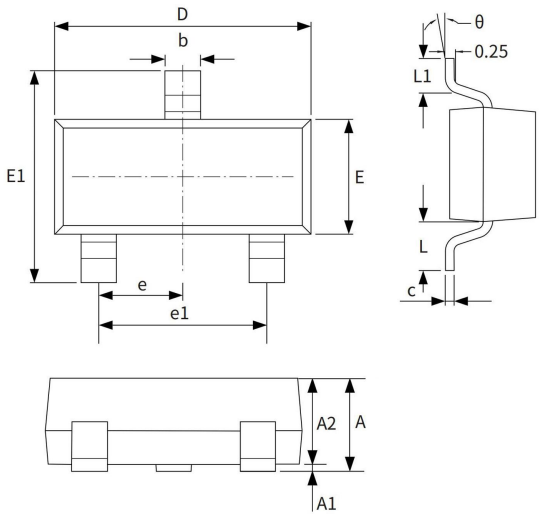
Figure 11. Transient Thermal Response Curve.

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Ordering Information

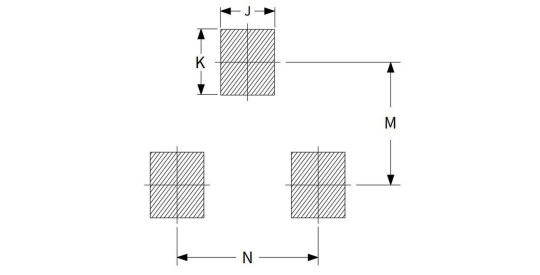
PACKAGE	PACKAGE CODE	UNIT WEIGHT(g)	REEL(pcs)	BOX(pcs)	CARTON(pcs)	DELIVERY MODE
SOT-23	R1	0.008	3000	30000	240000	7''

Package Outline Dimensions (SOT-23)



Symbol	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	0.90	1.15	0.035	0.045
A1	-	0.10	-	0.004
A2	0.90	1.05	0.035	0.041
b	0.30	0.50	0.012	0.020
c	0.10	0.20	0.004	0.008
D	2.80	3.00	0.110	0.118
E	1.20	1.40	0.047	0.055
E1	2.25	2.55	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.80	2.00	0.071	0.079
L	0.550REF		0.022REF	
L1	0.30	0.50	0.012	0.020
θ	-	8°	-	8°

Suggested Pad Layout



Symbol	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
J	0.75	0.85	0.030	0.033
K	0.85	0.95	0.033	0.037
M	1.95	2.05	0.077	0.081
N	1.85	1.95	0.073	0.077